Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5699	(soi "silicon-on-insulator" sos "silicon-on-sapphire" box (buried adj oxide) (silicon near epitax$8)) same (sige gesi (silicon near germanium))	US-PGPUB; USPAT	OR	ON	2005/02/05 19:45
L2	377	1 and ((source drain) with (elevat$10 rais$6))	US-PGPUB; USPAT	OR	ON	2005/02/05 19:45
L3	43	1 same ((source drain) with (elevat$10 rais$6))	US-PGPUB; USPAT	OR	ON	2005/02/05 19:22
L4	629	(soi "silicon-on-insulator" sos "silicon-on-sapphire" box (buried adj oxide) (silicon near epitax$8)) same (sige gesi (silicon near germanium))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 19:47
L6	21	1 same ((gate channel) near2 (recess$6 trench groove damascene inlaid "in-laid"))	US-PGPUB; USPAT	OR	ON	2005/02/05 19:41
L8	6	4 and ((gate channel) with (recess$6 trench groove damascene inlaid "in-laid"))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 19:49
L9	3	4 and ((source drain) same (elevat$10 rais$6))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 19:51
L10	5285	438/151.ccls. 438/270.ccls. 438/295.ccls. 438/300.ccls. 438/589.ccls. 438/595.ccls. 257/347.ccls. 257/387.ccls.	US-PGPUB; USPAT	OR	ON	2005/02/05 19:19
L13	80	2 and 10	US-PGPUB; USPAT	OR	ON	2005/02/05 19:53
L14	930	10 and ((gate channel) near2 (recess$6 trench groove damascene inlaid "in-laid"))	US-PGPUB; USPAT	OR	ON	2005/02/05 19:46
L15	75	1 and 14	US-PGPUB; USPAT	OR	ON	2005/02/05 20:36
L16	2958	(soi "silicon-on-insulator" "silicon-on-sapphire" box (buried adj oxide) (silicon near epitax$8)) same (sige gesi (silicon near germanium))	US-PGPUB; USPAT	OR	ON	2005/02/05 19:45
L17	242	16 and ((source drain) with (elevat$10 rais$6))	US-PGPUB; USPAT	OR	ON	2005/02/05 19:45
L18	292	16 and 10	US-PGPUB; USPAT	OR	ON	2005/02/05 19:46
L19	63	17 and 10	US-PGPUB; USPAT	OR	ON	2005/02/05 20:57

L20	49	17 and ((gate channel) near2 (recess$6 trench groove damascene inlaid "in-laid"))	US-PGPUB; USPAT	OR	ON	2005/02/05 21:08
L21	228	(soi "silicon-on-insulator" "silicon-on-sapphire" box (buried adj oxide) (silicon near epitax$8)) same (sige gesi (silicon near germanium))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 19:47
L22	302	(soi "silicon-on-insulator" "silicon-on-sapphire" box (buried adj oxide) (silicon near epitax$8)) and (sige gesi (silicon near germanium))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 19:48
L23	8	22 and ((gate channel) with (recess$6 trench groove damascene inlaid "in-laid"))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 21:15
L24	1	22 and ((source drain) same (elevat$10 rais$6))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 21:19
L26	2	jp-2001057429-$.did.	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/05 21:20